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Last Name = HAYASHI  
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Application#	Patent#	Status	Date Filed	Title	Inventor Name
11002338	Not Issued	030	12/03/2004	METHOD OF EVALUATING SEMICONDUCTOR DEVICE	HAYASHI, HIROKAZU
10283011	Not Issued	030	11/16/2004	SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME	HAYASHI, HIROKAZU
10931271	Not Issued	020	09/03/2004	ESD PROTECTION DEVICE MODELING METHOD AND ESD SIMULATION METHOD	HAYASHI, HIROKAZU
10780238	Not Issued	030	02/19/2004	EVALUATION TEG FOR SEMICONDUCTOR DEVICE AND METHOD OF EVALUATION	HAYASHI, HIROKAZU
10668261	Not Issued	030	09/24/2003	METHOD FOR MODELING SEMICONDUCTOR DEVICE AND NETWORK	HAYASHI, HIROKAZU
10652176	Not Issued	030	01/17/2002	METHOD FOR MODELING SEMICONDUCTOR DEVICE PROCESS	HAYASHI, HIROKAZU
02821400	Issued	150	06/27/2001	SOI STRUCTURE SEMICONDUCTOR DEVICE AND A FABRICATION METHOD THEREOF	HAYASHI, HIROKAZU
02781421	Issued	150	02/13/2001	METHOD FOR MODELING DIFFUSION OF IMPURITIES IN A SEMICONDUCTOR	HAYASHI, HIROKAZU
02512826	Issued	150	03/06/2000	A METHOD OF FABRICATING A SOI STRUCTURE SEMICONDUCTOR DEVICE	HAYASHI, HIROKAZU
02543860	Issued	150	02/08/1999	PROFILE EXTRACTION METHOD AND PROFILE EXTRACTION APPARATUS	HAYASHI, HIROKAZU
03140522	Issued	150	10/25/1993	PROJECTED IMAGE DISPLAYING APPARATUS AND A METHOD OF CORRECTING COLOR UNEVENNESS THEREIN	HAYASHI, HIROKAZU
07701632	Issued	150	05/15/1991	CATIONIC ELECTRODEPOSITION COATING COMPOSITION	HAYASHI, HIROKAZU
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